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**Semiconductor devices – Bias-temperature stability test for metal-oxide, semiconductor, field-effect transistors (MOSFET) –
Part 1: Fast BTI test for MOSFET**

**Dispositifs à semiconducteurs – Essai de stabilité de température en
polarisation pour transistors à effet de champ metal-oxyde-semiconducteur
(MOSFET) –
Partie 1: Essai rapide de BTI pour les MOSFET**



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CONTENTS

FOREWORD.....	4
INTRODUCTION.....	6
1 Scope.....	7
2 Normative reference.....	7
3 Terms and definitions.....	7
4 Test equipment.....	9
4.1 Equipment.....	9
4.1.1 Wafer prober.....	9
4.1.2 Measurement equipment.....	9
4.2 Recommendation for handling.....	10
5 Test sample.....	10
5.1 Sample.....	10
5.1.1 General.....	10
5.1.2 Channel length (gate length).....	10
5.1.3 Channel width (gate width).....	10
5.1.4 Structure.....	10
5.1.5 Wafer process.....	11
5.2 Antenna protection diode.....	11
5.3 Number of samples.....	11
6 Procedure.....	12
6.1 General remarks on measurement time.....	12
6.2 Definition of measurement parameter.....	12
6.2.1 Expression of degradation parameters.....	12
6.2.2 Measurement in weakly inverted region.....	13
6.2.3 Measurement in subthreshold region.....	13
6.2.4 Measurement of I_D degradation (I_{Dsat} , I_{Dlin}).....	14
6.3 Test.....	14
6.3.1 Test flow.....	14
6.3.2 Fast voltage switching.....	15
6.3.3 Temperature.....	16
6.3.4 Electric field strength E_{OX}	16
6.3.5 Read point.....	16
6.3.6 Total test time.....	16
6.4 Lifetime estimation.....	17
6.4.1 Procedure for estimating the degradation at end of life.....	17
6.4.2 Procedure for estimating the lifetime on the targeted criteria.....	18
Annex A (informative) Recovery effect of BTI.....	19
Annex B (informative) Selection of a wide device [2].....	20
Bibliography.....	22
Figure 1 – Degradation (ΔV_{th}) recovering by BTI conditions removing with time.....	6
Figure 2 – $I_D - V_{GS}$ curve to explain V_{th-ext}	8
Figure 3 – Connection between MOSFET electrodes and external terminals.....	10
Figure 4 – Example of antenna protection circuit for BULK process.....	11
Figure 5 – Measurement time dependence of recovery effect.....	12

Figure 6 – Calculation method of V_{th} degradation	14
Figure 7 – Comparison of BTI flowchart	15
Figure 8 – Switching schematic of fast BTI.....	16
Figure A.1 – Recovery time dependence of Pch BTI	19
Figure B.1 – Typical BTI induced variance dependence on W	21
Figure B.2 – Possible MOSFET layout to be adopted with narrow device	21

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**SEMICONDUCTOR DEVICES –
BIAS-TEMPERATURE STABILITY TEST FOR METAL-OXIDE,
SEMICONDUCTOR, FIELD-EFFECT TRANSISTORS (MOSFET) –**

Part 1: Fast BTI test for MOSFET

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The text of this International Standard is based on the following documents:

FDIS	Report on voting
47/2627/FDIS	47/2637/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 62373 series, published under the general title *Semiconductor devices – Bias-temperature stability test for metal-oxide, semiconductor, field-effect transistors (MOSFET)*, can be found on the IEC website.

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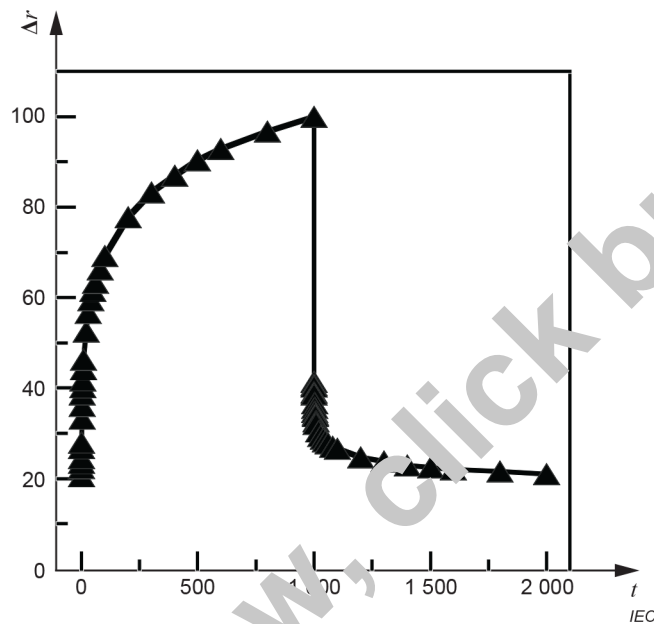
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INTRODUCTION

BTI (bias temperature instability) degradation of semiconductor devices is a crucial failure. IEC 62373:2006 provides a method to test for this failure.

With advances in technology, the magnitude of recovery for BTI degradation has been remarkable. Recovery from BTI degradation occurs in microseconds to milliseconds after removing or reducing gate stress. Figure 1 below shows experiment data of V_{th} shift which is stressed in BTI condition for 1 000 s and not stressed after that [1]¹. It shows that the degradation is rapidly recovered, to about 40 % in a few seconds right after removing the stress at 1 000 s. Therefore, a fast measurement method is necessary to avoid this effect and to determine this degradation with exactitude.



Key

Δr ratio of V_{th} degradation amount to maximum degradation;

t stress or recovery time, expressed in seconds.

Figure 1 – Degradation (ΔV_{th}) recovering by BTI conditions removing with time

However, the existing test, described in IEC 62373, suffers from the disadvantage that the recovery process starts as soon as the stress is reduced while making the fairly lengthy set of measurements that establish the shift in threshold voltage. The procedure described in this standard uses an alternative method for measuring degradation that, by taking very little time, minimizes the partial recovery that occurs during the measurement.

¹ Numbers in square brackets refer to the Bibliography.

SEMICONDUCTOR DEVICES – BIAS-TEMPERATURE STABILITY TEST FOR METAL-OXIDE, SEMICONDUCTOR, FIELD-EFFECT TRANSISTORS (MOSFET) –

Part 1: Fast BTI test for MOSFET

1 Scope

This part of IEC 62373 provides the measurement procedure for a fast BTI (bias temperature instability) test of silicon based metal-oxide semiconductor field-effect transistors (MOSFETs).

This document also defines the terms pertaining to the conventional BTI test method.

2 Normative reference

There are no normative references in this document.

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

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- ISO Online browsing platform: available at <http://www.iso.org/obp>

3.1

nominal power supply voltage

V_{DD}

suitable value of the voltage used to designate the power supply of the technology

3.2

drain – source voltage

V_{DS}

voltage between the drain and the source

3.3

gate – source voltage

V_{GS}

voltage between the gate and the source

3.4

well – source voltage

V_{BS}

voltage between the well and the source

3.5

drain current

I_D

current monitored for drain terminal when V_{BS} is zero